

### N-channel SiC power MOSFET

$V_{\rm DSS}$	1200V
R <sub>DS(on)</sub> (Typ.)	$80$ m $\Omega$
I <sub>D</sub>	31A
$P_D$	165W

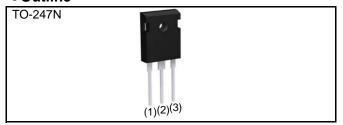
#### Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

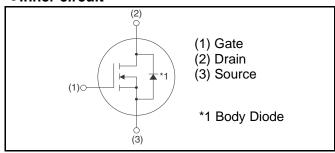
### Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

#### Outline



#### ●Inner circuit



Packaging specifications

Packing		Tube				
	Reel size (mm)	-				
Type	Tape width (mm)	-				
Туре	Basic ordering unit (pcs)	30				
	Taping code	C11				
	Marking	SCT3080KL				

### ◆Absolute maximum ratings (T<sub>a</sub> = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		$V_{DSS}$	1200	V
Continuous drain current	T <sub>c</sub> = 25°C	l <sub>D</sub> *1	31	А
Continuous arain current	T <sub>c</sub> = 100°C	l <sub>D</sub> *1	22	А
Pulsed drain current		l <sub>D,pulse</sub> *2	77	А
Gate - Source voltage		$V_{GSS}$	−4 to 22	V
Gate-Source Surge Voltage		$V_{GSS\_surge}$	-4 to 22	V
Recommended Drive Voltage		$V_{GS\_op}$	0 / 18	V
Junction temperature		T <sub>j</sub>	175	°C
Range of storage temperature		T <sub>stg</sub>	-55 to +175	°C

### ●Thermal resistance

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R <sub>thJC</sub>	-	0.70	0.91	°C/W

## ●Electrical characteristics (T<sub>a</sub> = 25°C)

Doromotor	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = 1mA$	1200	-	-	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I <sub>DSS</sub>	T <sub>j</sub> = 25°C	-	1	10	μΑ
		T <sub>j</sub> = 150°C	-	2	-	
Gate - Source leakage current	I <sub>GSS+</sub>	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I <sub>GSS</sub> _	$V_{GS} = -4V$ , $V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = 10V$ , $I_D = 5mA$	2.7	-	5.6	V
		$V_{GS} = 18V, I_D = 10A$				
Static drain - source on - state resistance	R <sub>DS(on)</sub> *3	T <sub>j</sub> = 25°C	-	80	104	mΩ
		T <sub>j</sub> = 125°C	-	120	-	
Gate input resistance	$R_{G}$	f = 1MHz, open drain	-	12	-	Ω

### ●Example of acceptable Vgs waveform



# ●Electrical characteristics (T<sub>a</sub> = 25°C)

Darameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g <sub>fs</sub> *3	$V_{DS} = 10V, I_{D} = 10A$	-	4.4	-	S
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0V$	-	785	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	75	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	35	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	$V_{GS} = 0V$ $V_{DS} = 0V$ to 600V	-	74	-	pF
Turn - on delay time	t <sub>d(on)</sub> *3	$V_{DD} = 400V, I_{D} = 10A$	-	15	1	
Rise time	t <sub>r</sub> *3	V <sub>GS</sub> = 18V/0V	-	22	-	no
Turn - off delay time	t <sub>d(off)</sub> *3	$R_L = 40\Omega$	-	29	-	ns
Fall time	t <sub>f</sub> *3	$R_G = 0\Omega$	-	24	-	
Turn - on switching loss	E <sub>on</sub> *3	$V_{DD} = 600V, I_{D} = 10A$ $V_{GS} = 18V/0V$	-	132	-	1
Turn - off switching loss	E <sub>off</sub> *3	R <sub>G</sub> = 0Ω L=750μH *E <sub>on</sub> includes diode reverse recovery	-	18	-	μJ

# •Gate Charge characteristics ( $T_a = 25$ °C)

Parameter Syml	Symbol	mbol Conditions -	Values			Unit
	Syllibol		Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*3}$	V <sub>DD</sub> = 600V	-	60	1	
Gate - Source charge	Q <sub>gs</sub> *3	I <sub>D</sub> = 10A	-	15	-	nC
Gate - Drain charge	$Q_{gd}^{*3}$	V <sub>GS</sub> = 18V	-	25	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} = 600V, I_D = 10A$	-	9.6	-	V

<sup>\*1</sup> Limited only by maximum temperature allowed.

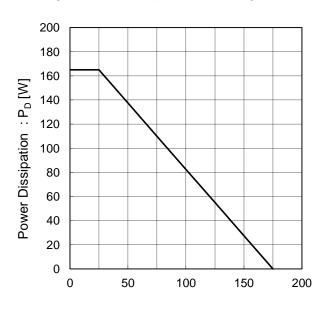
<sup>\*2</sup> PW  $\leq$  10  $\mu s,$  Duty cycle  $\leq$  1%

<sup>\*3</sup> Pulsed

# ●Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

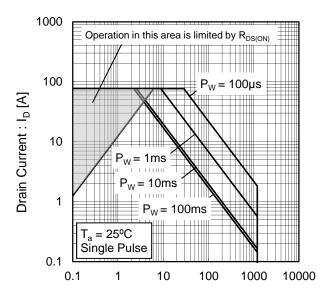
Doromotor	Parameter Symbol Conditions	Conditions	Values			Unit
raiametei		Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l <sub>S</sub> *1	-T <sub>c</sub> = 25°C	-	1	31	А
Inverse diode direct current, pulsed	I <sub>SM</sub> *2		-	-	77	А
Forward voltage	V <sub>SD</sub> *3	$V_{GS} = 0V, I_{S} = 10A$	-	3.2	ı	V
Reverse recovery time	t <sub>rr</sub> *3	I <sub>F</sub> =10A, V <sub>R</sub> = 600V di/dt = 1100A/μs	-	17	ı	ns
Reverse recovery charge	Q <sub>rr</sub> *3		-	50		nC
Peak reverse recovery current	I <sub>rrm</sub> *3		-	6	-	А

Fig.1 Power Dissipation Derating Curve



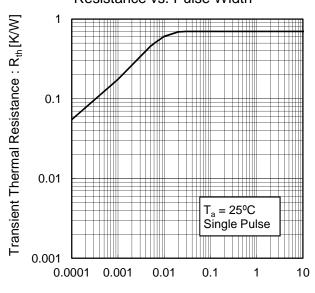
Junction Temperature : T<sub>i</sub> [°C]

Fig.2 Maximum Safe Operating Area



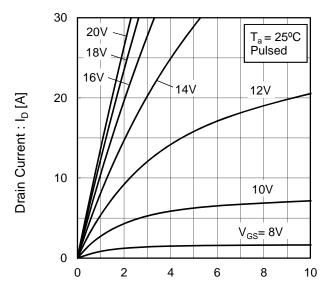
Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



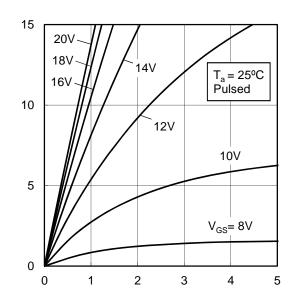
Pulse Width :  $P_W$  [s]

Fig.4 Typical Output Characteristics(I)



Drain - Source Voltage : V<sub>DS</sub> [V]

Fig.5 Typical Output Characteristics(II)

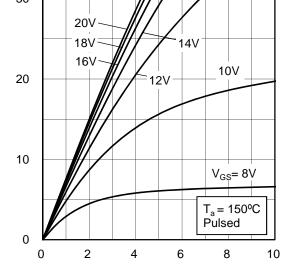


Drain Current: I<sub>D</sub> [A]

Drain - Source Voltage : V<sub>DS</sub> [V]

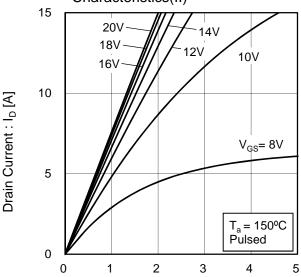


Drain Current: I<sub>D</sub> [A]



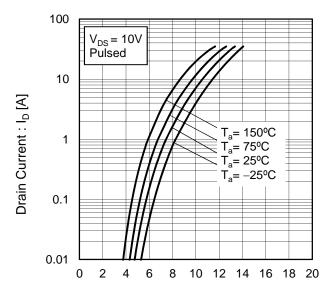
Drain - Source Voltage :  $V_{DS}$  [V]

Fig.7 T<sub>j</sub> = 150°C Typical Output Characteristics(II)



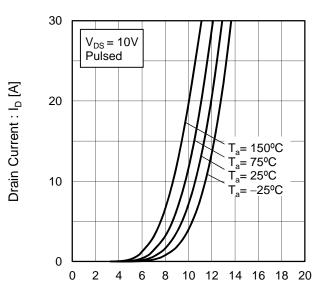
Drain - Source Voltage :  $V_{DS}$  [V]

Fig.8 Typical Transfer Characteristics (I)



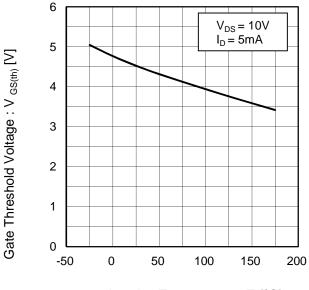
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.9 Typical Transfer Characteristics (II)



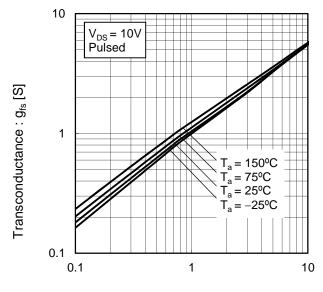
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.10 Gate Threshold Voltage vs. Junction Temperature

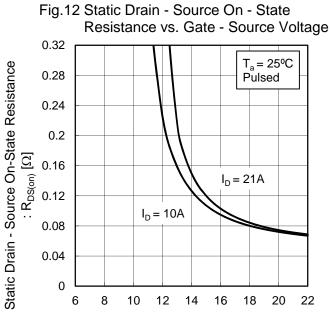


Junction Temperature : T<sub>i</sub> [°C]

Fig.11 Transconductance vs. Drain Current



Drain Current : I<sub>D</sub> [A]



Gate - Source Voltage : V<sub>GS</sub> [V]

Resistance vs. Junction Temperature 0.32 V<sub>GS</sub> = 18V Pulsed Static Drain - Source On-State Resistance 0.28 0.24 0.2  $: R_{\mathsf{DS}(\mathsf{on})} \left[ \Omega \right]$ 0.16  $I_{D} = 21A$ 0.12 0.08  $I_{D} = 10A$ 0.04 0 -50 0 50 100 150 200

Junction Temperature : T<sub>i</sub> [°C]

Fig.13 Static Drain - Source On - State

Drain Current: I<sub>D</sub> [A]



Fig.15 Typical Capacitance vs. Drain - Source Voltage

10000  $C_{iss}$ 1000  $C_{oss}$   $C_{rss}$   $C_{rss}$   $C_{rss}$   $C_{rss}$ 

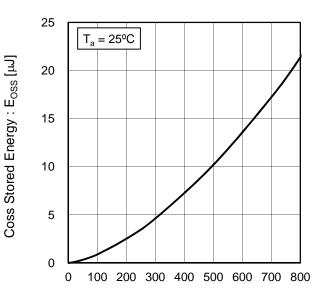
Drain - Source Voltage : V<sub>DS</sub> [V]

100

1000

10

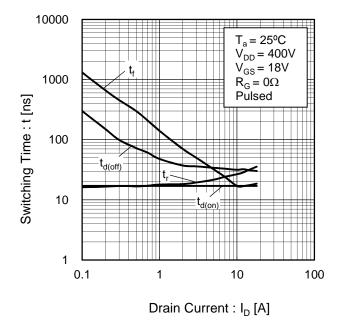
Fig.16 Coss Stored Energy



Drain - Source Voltage : V<sub>DS</sub> [V]

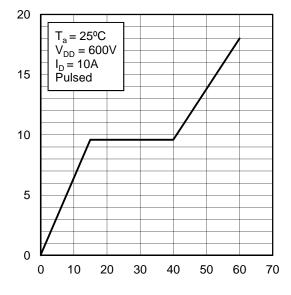
Fig.17 Switching Characteristics

0.1

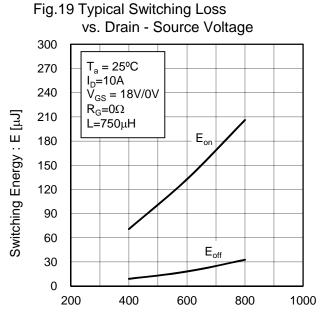


Gate - Source Voltage : V<sub>GS</sub> [V]

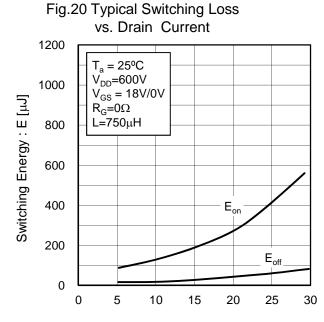
Fig.18 Dynamic Input Characteristics



Total Gate Charge : Q<sub>g</sub> [nC]



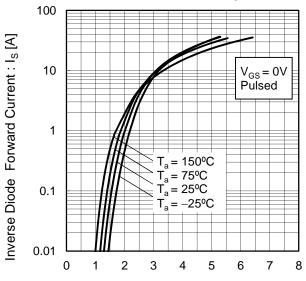
Drain - Source Voltage : V<sub>DS</sub> [V]



Drain Current: I<sub>D</sub> [A]

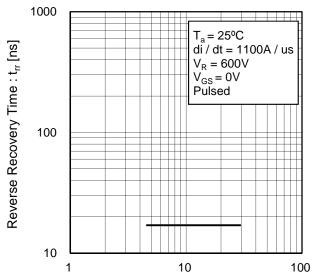
Fig.21 Typical Switching Loss vs. External Gate Resistance 1200  $T_a = 25^{\circ}C$ 1000 V<sub>DD</sub>=600V  $I_D = 10A$  $\tilde{V}_{GS} = 18V/0V$ Switching Energy: E [µJ] 800 L=750μH 600 400  $\mathsf{E}_{\mathsf{on}}$ 200  $\mathsf{E}_{\mathsf{off}}$ 0 5 10 15 20 25 30 0

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I<sub>S</sub> [A]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

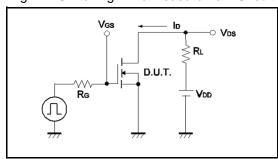


Fig.2-1 Gate Charge Measurement Circuit

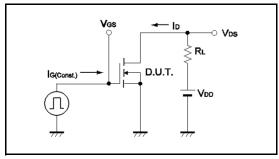


Fig.3-1 Switching Energy Measurement Circuit

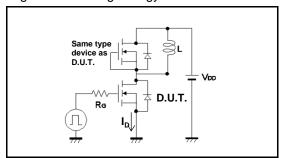


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

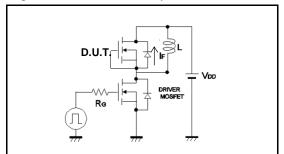


Fig.1-2 Switching Waveforms

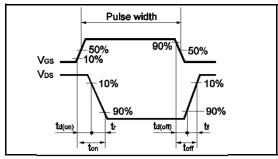


Fig.2-2 Gate Charge Waveform

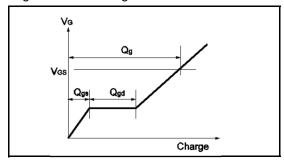
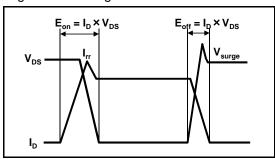
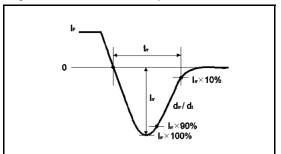


Fig.3-2 Switching Waveforms





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# SCT3080KL - Web Page

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Part Number	SCT3080KL
Package	TO-247N
Unit Quantity	450
Minimum Package Quantity	30
Packing Type	Tube
Constitution Materials List	inquiry
RoHS	Yes